IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent Application of	)
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TSUCHIYA et al.	)
	)
Application Number: To be Assigned	)
	)
Filed: Concurrently Herewith	)
	)
For: SEMICONDUCTOR OPTICAL DEVICES AND OPTICAL MODULES	)
	)
ATTORNEY DOCKET NO. NITT.0194	)

Honorable Assistant Commissioner
for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, this Information Disclosure Statement is submitted in the above-identified patent application. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each U.S. and foreign patent, or each publication or portion thereof listed or herein identified, submitted herewith.

This Information Disclosure Statement is submitted with the initial filing of the application. Accordingly, no fee is due or payable at this time.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

Please charge any additional fees or credit any overpayments in connection with this paper to Deposit Account No. 08-1480.

Respectfully submitted,

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U.S. Department of Commerce Patent and Trademark Office	APPLICANT TSUCHIYA et al.	
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U.S. Patent Documents

Examiner Initial		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE

Foreign Patent Documents

Examiner Initial		DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO
		10-84170	8/11/97	Japan			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

		R. Bhat et al, "High-Performance 1.3 μm AlGaInAs/InP Strained Quantum Well Lasers Grown by Organometallic Chemical Vapor Deposition", Journal of Crystal Growth (1004), pp. 858-865
		P.J.A. Thijs et al., "High Performance Buried Heterostructure λ=1.5 μm InGaAs/AlGaInAs Strained-Layer Quantum Well Laser Diodes", 10th International Conference on Indium Phosphide and Related Materials (1996) ThA2-2, pp. 765-768
		Tawee Tanbun-Ek et al., "High Performance Buried Heterostructure 1.55 μm Wavelength AlGaInAs/InP Multiple Quantum Well Lasers Grown Entirely by NOVPE Technique", 10th International Conference on Indium Phosphide and Related Materials (May 1998) ThP-48, pp. 702-705
		C. E. Zah et al., "High-Temperature Modulation Dynamics of 1.3 μm $Al_xGa_y In_{1-x-y}As$/InP Compressive-Strained Multiple-Quantum-Well Lasers", 14th International Semiconductor Laser Conference (1994), TH 1.3, pp. 215-216

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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